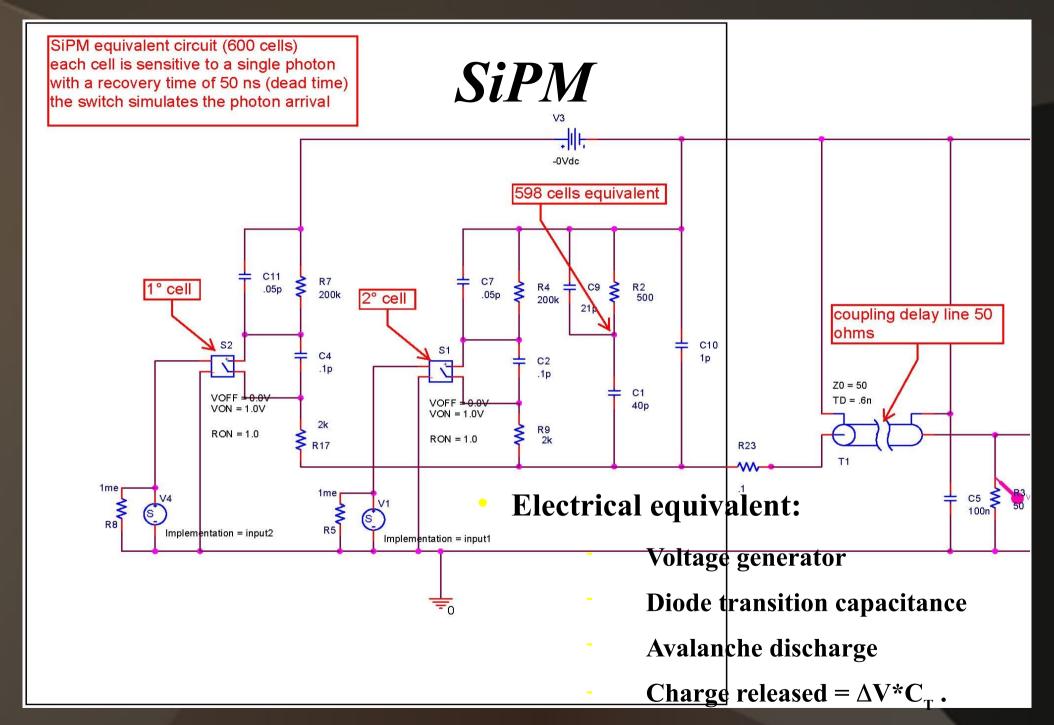
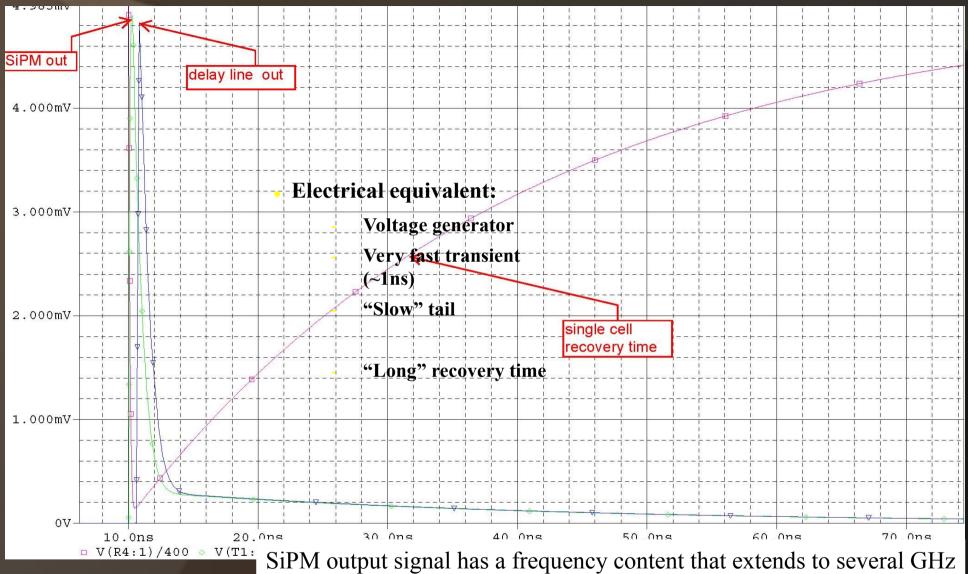
# Perspectives for the MuRay experiment electronics

- Scintillator bars detect muon passage
- SiPM used coupled with WLS (Wavelength Shifters)
- SPIROC based Read Out
- Hybrid with SiPM
- Next: EASIROC chip
  - Better adapted to asynchronous operation
  - Greater granularity for a more versatile triggering
  - Less components integrated on a die
    - Lower power consumption
    - More flexibility in deployment





## SiPM signal characteristics



In order to qualify SiPM timing characteristics a very high speed set-up is needed (WORK IN PROGRESS IN FLORENCE, now well advanced)

## Full SiPM characterization

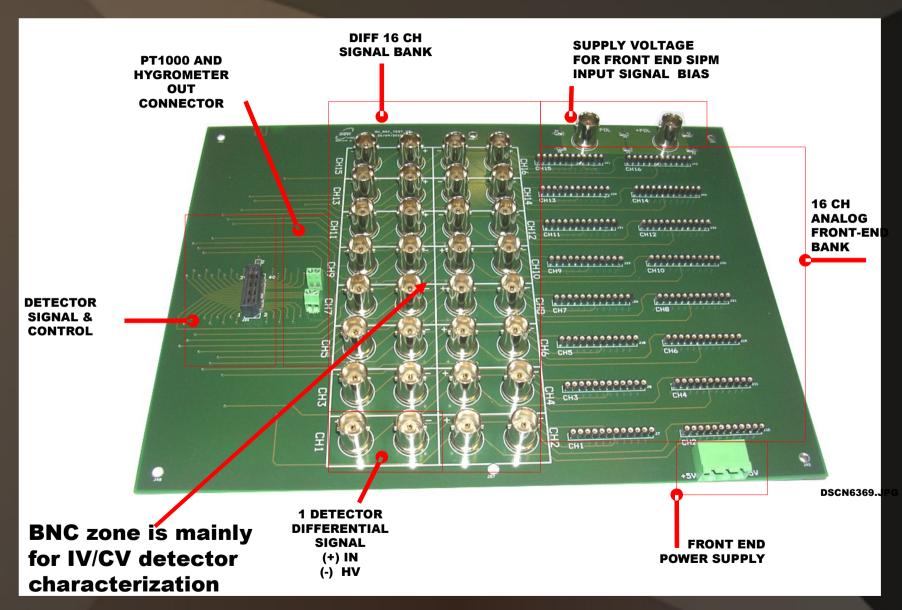
- Full characterization of the SiPM can be divided in three 'stages':
- Static:
  - Includes forward and reverse IV and CV measurements
- Dynamic:
  - Includes dark count, gain, afterpusle probability, optical crosstalk measurements and temporal characterization
- Optical:
  - Includes spectral sensitivity and photon detection efficiency measurements

*Two setups developed (and mixed .....):* 

One dedicated to single SiPM characterizations, with custom electronics and temperature control, and one using MuRay hybrids and EASIROC chip and MuRay developed test boards.

Results presented have been obtained from both setups and/or a mixture of the two.

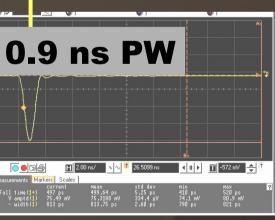
## I-V, C-V and signal TEST PCB

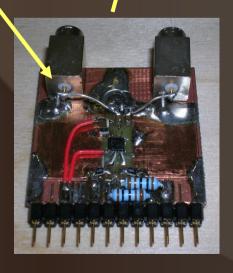


# Experimental Set-Up (MuRay hybrid for SiPM)









Relatively "slow" electronics Setup used also for IV and CV

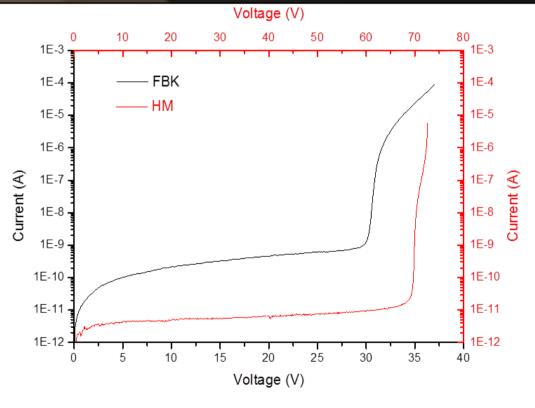
For some of these tests we have used also a modified hybrid. This modification allows connecting to hybrid single encapsulated SiPM

Two devices have been used for this test:

- 1 FBK IRST described above, packed up in TO case
- 2 Hamamatsu S10362-11-050U series in metal package. It has 400 cells with dimension 50x50 micron<sup>2</sup> and its total active area is 1 mm<sup>2</sup>.

Both devices have been electrically characterized. This characterization includes forward and reverse IV and CV measurements.

	FBK	Hamamatsu
$ m V_{_{BD}}$	29.25 V	69.7 V
Working region	> 6 V	~ 2V
Current	Up to 10e <sup>-4</sup> A	Up to 10e <sup>-6</sup> A
$\mathbf{R}_{ ext{q}}$	650 kOhm	129 kOhm
C	51 pF	36 pF

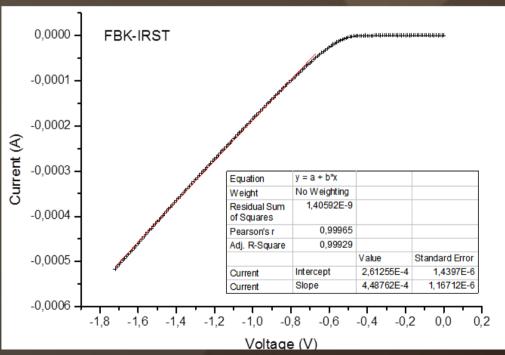


Reverse IV curves for Hamamatsu and FBK at 20 °C.

### Forward IV

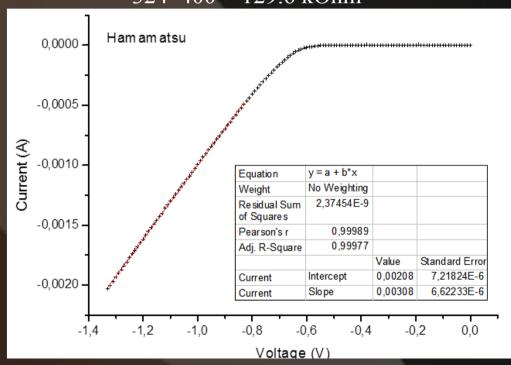
Total resistance is 2228 Ohm. Quenching resistor is

2228\*292 = 650.6 kOhm

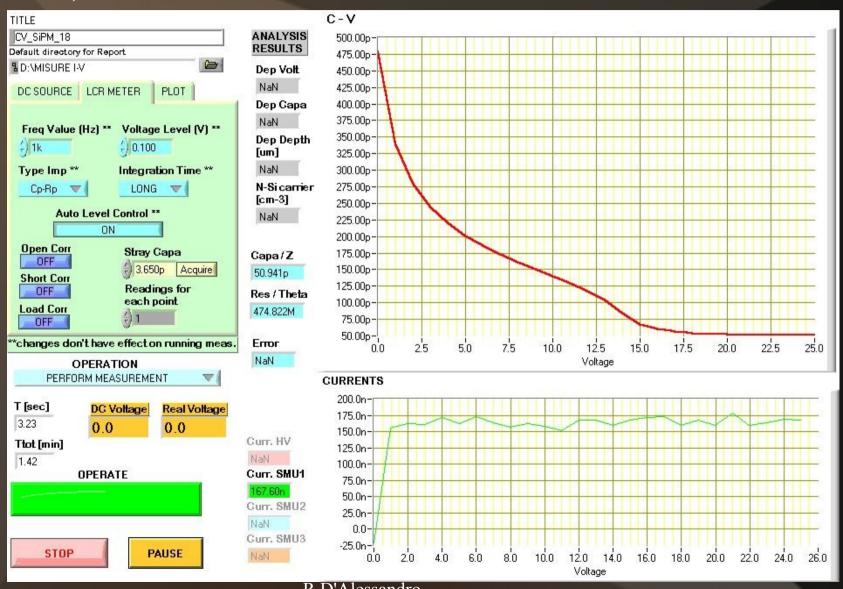


Total resistance is 324 Ohm. Quenching resistor is

324\*400 = 129.6 kOhm

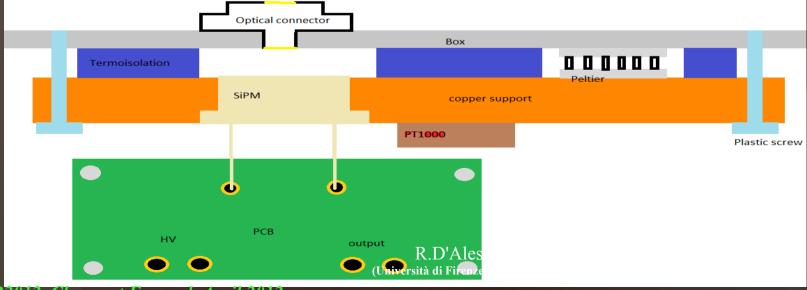


### CV (FBK)



## Experimental Set-Up (Single SiPM)

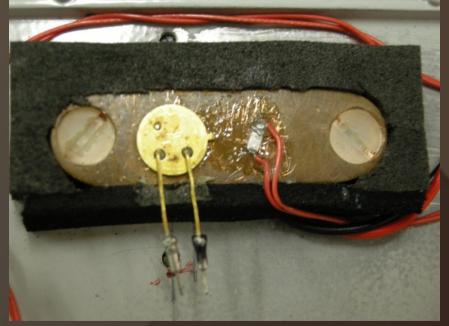
- Set of instruments for IV and CV measurements;
  - HP 4142B, HP 4284 (Precision Voltage Source, Precision LCR meter (20Hz-1MHz)
- Fast preamlifier and oscilloscope;
  - Tektronix, various models Max 1GHz BW.
  - LeCroy SDA 760Zi: 6 GHz, 40 GS/s (Only arrived now!) Most of the results presented were obtained with less performant scopes.
  - Custom preamplifiers: G = 1-10, bandwidth from 0.3 to 3 GHz
- Fast laser;
  - pulse laser 76 MHz, 4 ps, 600 nm
  - Laser support equipment
- Mechanical support for temperature control, electrical and optical connections



## Experimental Set-Up for FBK

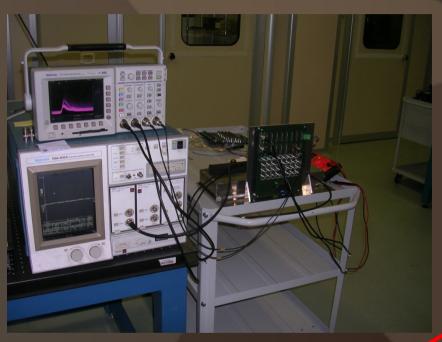
- The present data refers to the Silicon Photomultiplier by FBK-IRST for the MuRay project.
- This device has been packaged and bonded in our laboratory.
- We have used an opened TO case as package.

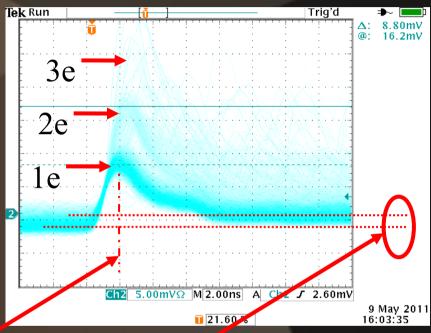
The SIPM has 292 cells of  $70x70 \mu^2$  and a total active area of 1.54 mm<sup>2</sup>





## LAB Test with Thermal Electron

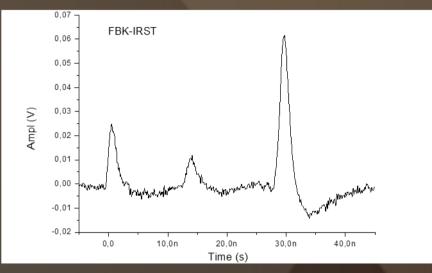


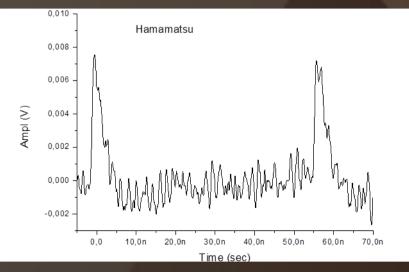


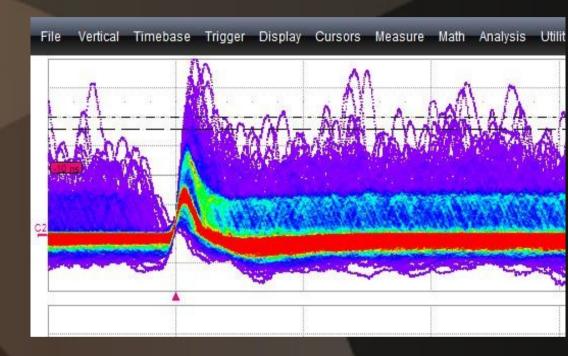
Peak amplidue and peak time degradation caused by insufficient bandwidth scope

Baseline difference due to SLOW TAIL SiPM response

### Signal characterization with single -channel custom preamplifier ("slow")



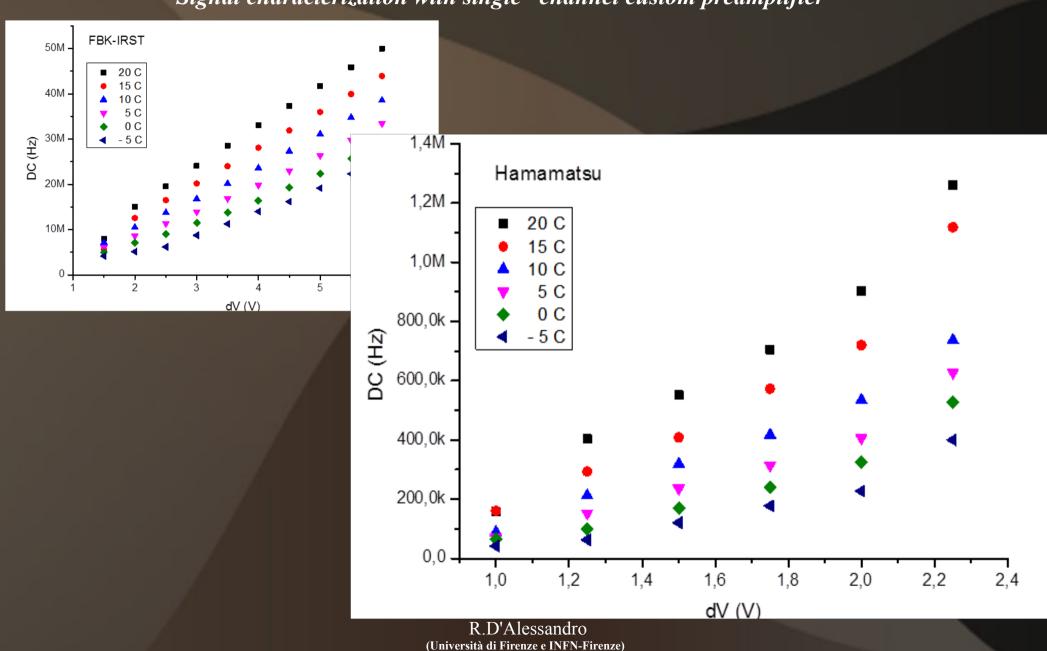




Rise time for both sensors is about of 550 ps

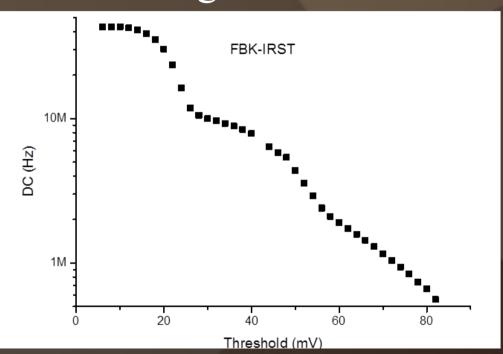
Preamplifier makes some signal distortion (negative overshoot on the trailing edge of the pulse)

Signal characterization with single -channel custom preamplifier

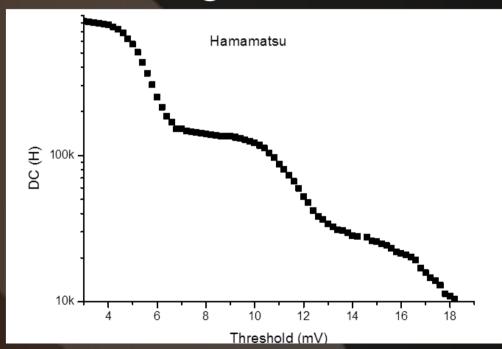


Dark count rate vs threshold (obtained with LeCroy SDA 760Z): 6 GHz)

DC at 20 °C and 5,5 V overvoltage

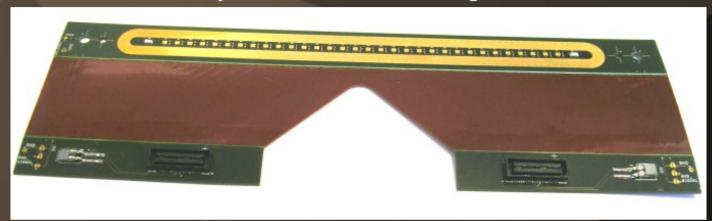


## DC at 20 °C and 2 V overvoltage



## New hybrid support for SiPM

Improved flexibility for front-end acquisition board.

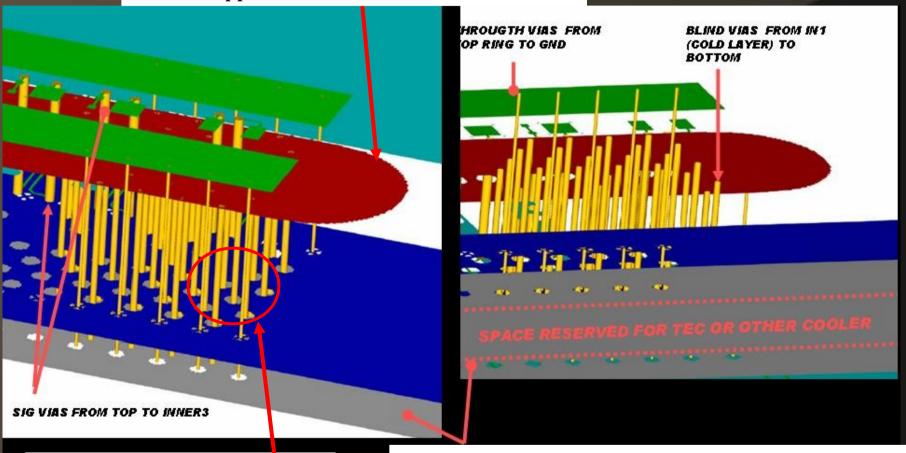


Thermal connection between the TE cooler (Peltier) and the inner cold metal has been improved with a lot of vias.



## Thermal configuration - SiPM side

**INNER copper PLATE 75um from SiPM Bottom** 



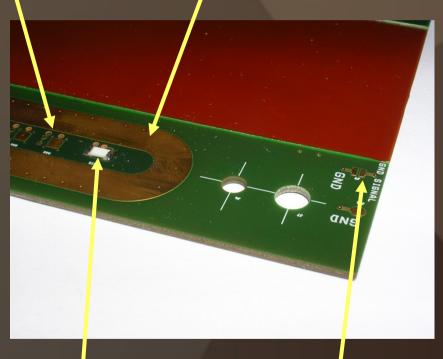
Copper vias to improve thermal conducibility between bottom cold plate and inner plate below SiPM

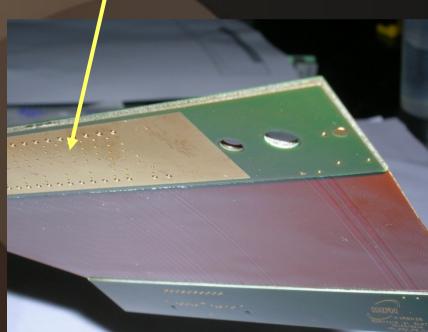
**BOTTOM PLANE (COLD LAYER)** 

## Detailed view of SiPM side

SiPM bonding PAD

Anular ring to create an isolated volume from outside Copper plate for cooling SiPM bottom side

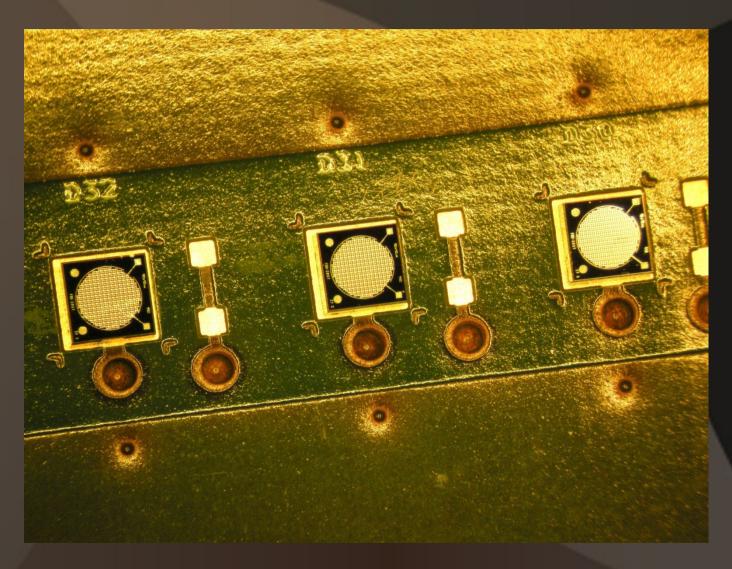




PT1000 temperature sensor

GND jumper

## Hybrid SiPM side complete



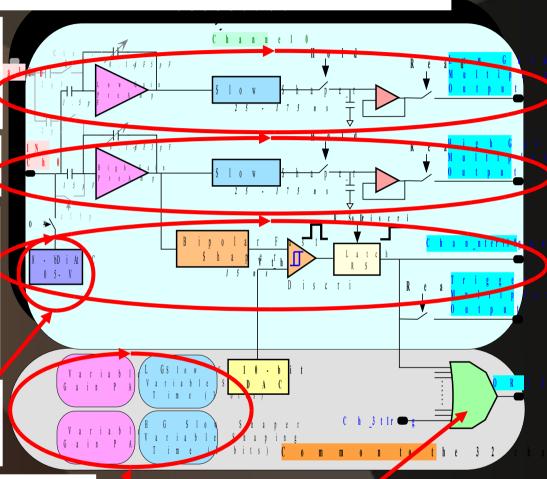
## «EASIROC»

### **EASIROC 32 CH ASIC HAS THREE MAIN FUNCTIONS:**

- 1) 32 CH LOW GAIN, PROGRAMMABLE SHAPING, VOLTAGE MEASUREMENT PATH THAT HAS SAMPLE AND HOLD CAPABILITY
- 2) 32 CH HIGH GAIN, PROGRAMMABLE SHAPING, LIKE PREVIOUS ONE
- 3) 32 CH FAST TIMING PATH, WITH COMMON THRESHOLD PROGRAMMABLE COMPARATOR WITH 32 OUTPUTS. MAIN DATA IN TIMING APPLICATION AND ARE FED TO THE FPGA CHIP TO BE PROCESSED AS REQUESTED.

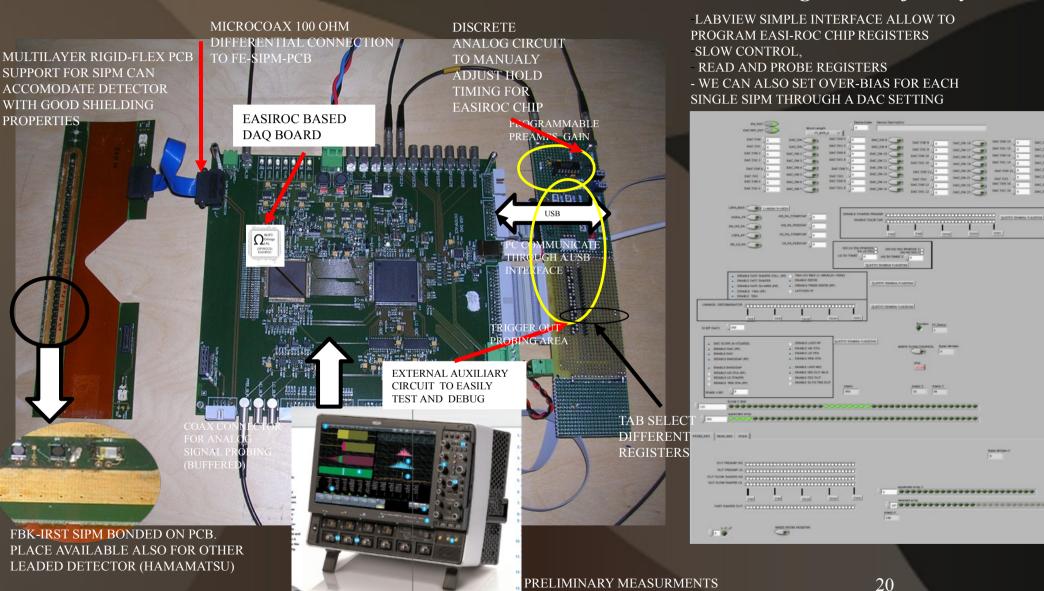
SIPM BIAS VOLTAGE CAN BE PRECISELY ADJUSTED FOR EACH CHANNEL BY A PROGRAMMABLE 5V DAC

IN ORDER TO PROPERLY CONFIGURE AND PROGRAMM THE CHIP, 3 REGISTERS CAN BE SERIALLY ACCESSED: «SLOW CONTROL» REG, »READ» REG., «PROBE» REG.



«OR32» FAST SIGNAL USED TO TRIGGER ACQUISITION SEQUENCE

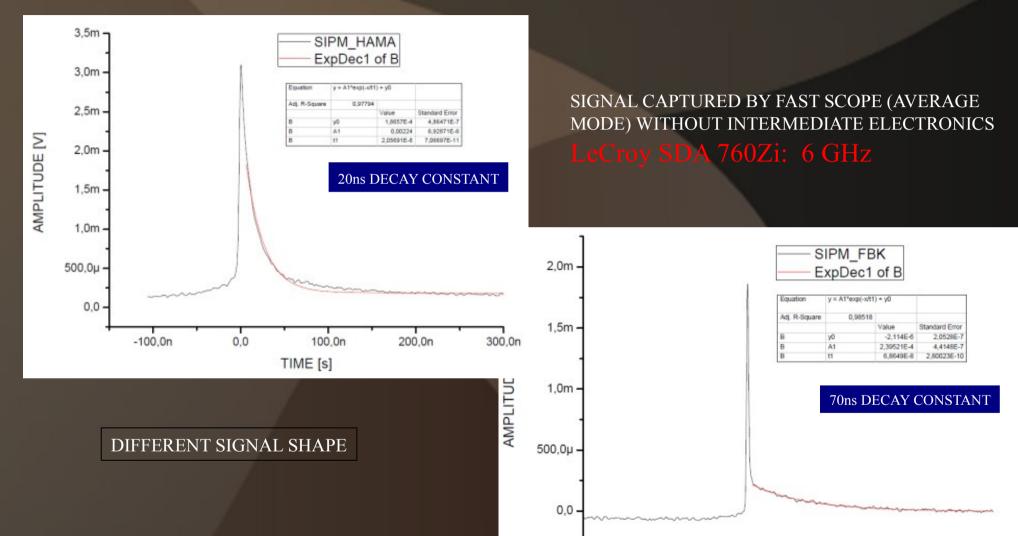
### SIPM TEST SET-UP using the modified hybrid



R.D'Alessandro (Università di Firenze e INFN-Firenze)

MADE WITH A FAST SCOPE

#### SIPM SIGNAL INPUT TO EASIROC



R.D'Alessandro (Università di Firenze e INFN-Firenze)

-200.0n

-100,0n

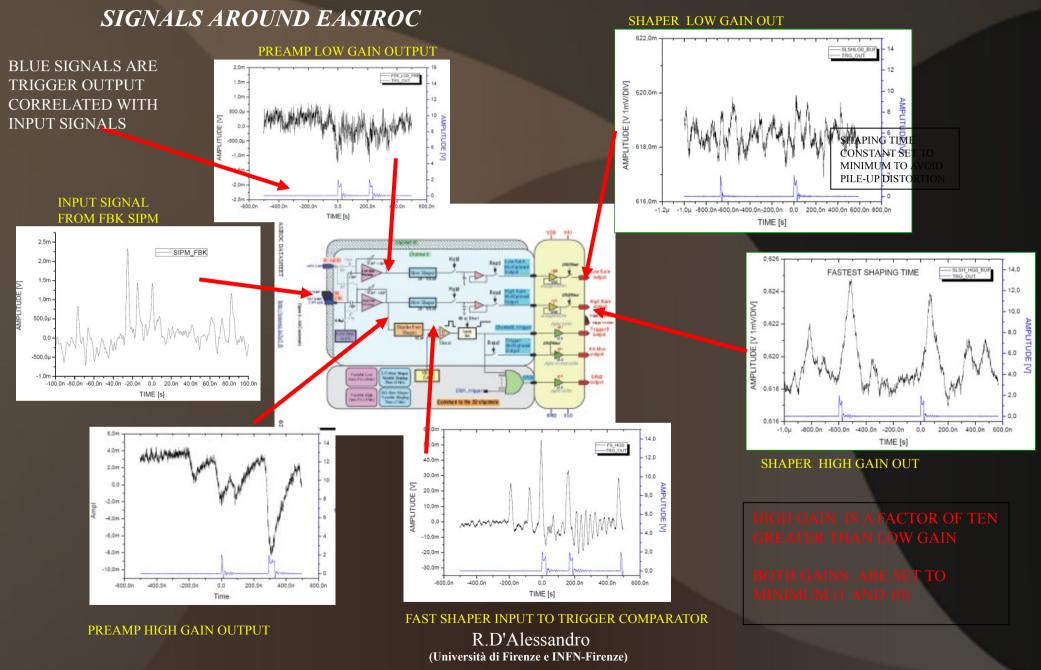
0.0

TIME [s]

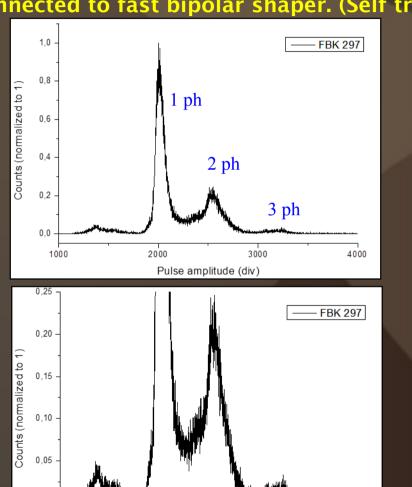
100.0n

200.0n

300.0n



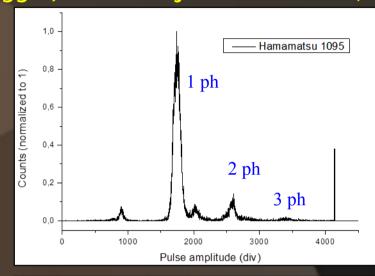
Pulse amplitude distribution for both devices measured with (EASIROC) probe connected to fast bipolar shaper. (Self trigger, threshold just above noise).

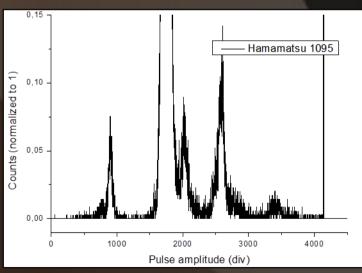


3000

Pulse amplitude (div)

4000

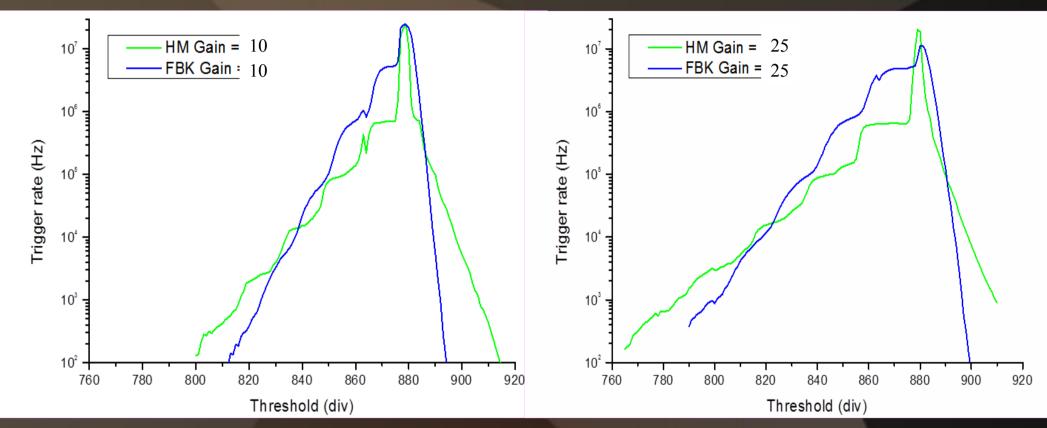




R.D'Alessandro (Università di Firenze e INFN-Firenze)

1000

Trigger pulse rate vs threshold for both devices at two values of high gain preamlifier



## Conclusions

- Our collaboration is now capable of performing a full characterization of SiPM devices.
- First results with EASIROC chip coupled to SiPM for MuRay are very encouraging.
- Will now finalise and build 16 new DAQ boards for the MuRay 1m<sup>2</sup> telescope.